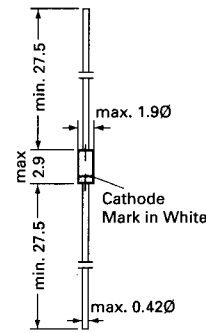


1N 4148M

SILICON EPITAXIAL PLANAR DIODE

Silicon Expitaxial Planar Diode
fast switching diode.



Glass case JEDEC DO-34

Dimensions in mm

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

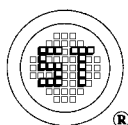
	Symbol	Value	Unit
Reverse Voltage	V_R	50	V
Peak Reverse Voltage	V_{RM}	60	V
Rectified Current (Average) Half Wave Rectification with Resist. Load at $T_{amb} = 25^\circ\text{C}$ and $f \geq 50\text{ Hz}$	I_0	130 ¹⁾	mA
Surge Forward Current at $t < 1\text{ s}$ and $T_j = 25^\circ\text{C}$	I_{FSM}	500	mA
Power Dissipation at $T_{amb} = 25^\circ\text{C}$	P_{tot}	400 ¹⁾	mW
Junction Temperature	T_j	200	$^\circ\text{C}$
Storage Temperature Range	T_s	-65 to + 200	$^\circ\text{C}$

¹⁾ Valid provided that leads at a distance of 8 mm from case are kept at ambient temperature

Characteristics at $T_j = 25^\circ\text{C}$

	Symbol	Min.	Typ.	Max.	Unit
Forward Voltage at $I_F = 100\text{ mA}$	V_F	-	-	1.1	V
Leakage Current at $V_R = 50\text{ V}$	I_R	-	-	0.5	μA
Reverse Breakdown Voltage tested with 100 μA Pulses	$V_{(BR)R}$	60	-	-	V
Capacitance at $V_F = V_R = 0$	C_{tot}	-	-	3	pF
Reverse Recovery Time from $I_F = 10\text{ mA}$ to $I_R = 1\text{ mA}$, $V_R = 6\text{ V}$, $R_L = 100\ \Omega$,	t_{rr}	-	-	4	ns

¹⁾ Valid provided that leads at a distance of 8 mm from case are kept at ambient temperature



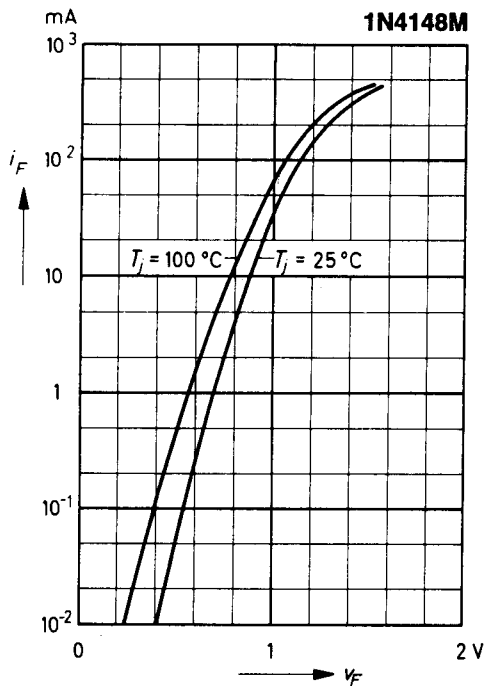
SEMTECH ELECTRONICS LTD.
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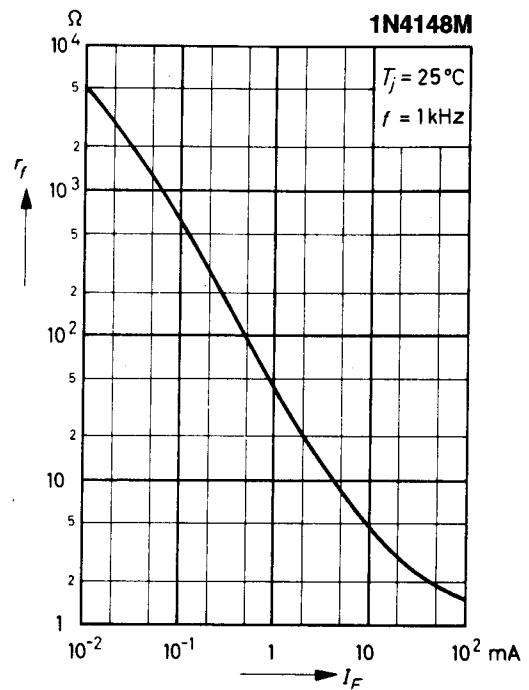
1N 4148M

SILICON EPITAXIAL PLANAR DIODE

Forward characteristics

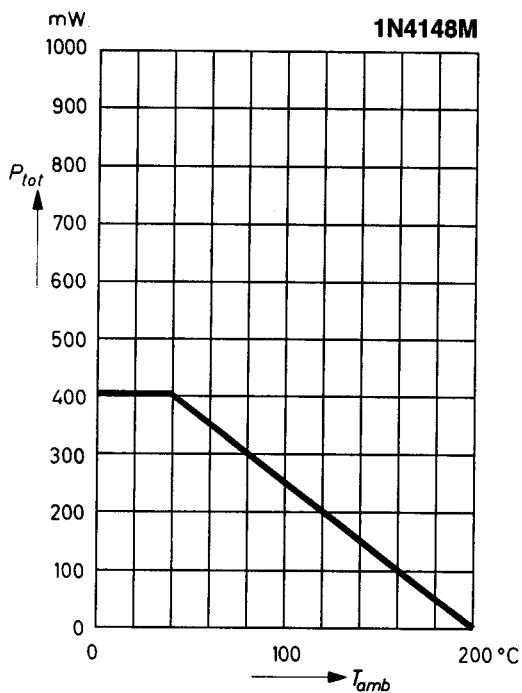


Dynamic forward resistance versus forward current

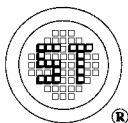
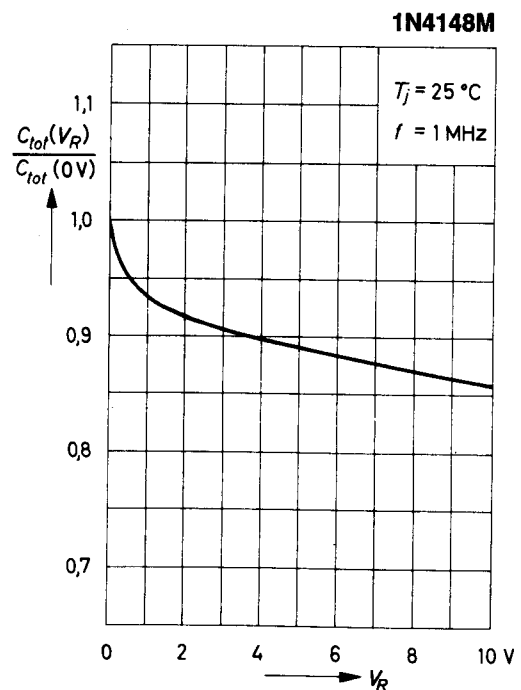


Admissible power dissipation versus ambient temperature

Valid provided that electrodes are kept at ambient temperature



Relative capacitance versus reverse voltage



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ISO 9002:94
Certificate No. 08C-0558